600mA 10kV -High Voltage Power Diodes

High reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

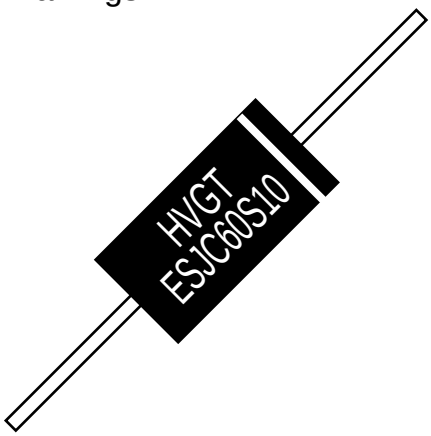
Features

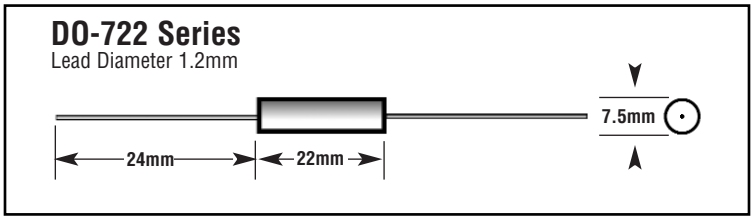
- High speed switching
- Epoxy resin molded in vacuum, Have anticorrosion in the surface
- High surge resisitivity for CRT discharge
- High reliability design
- Avalanche characteristic

Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power
- General purpose high voltage rectifier, Voltage multiplier assembly.

Outline Drawings :





Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Condition	ESJC60S10	Units
Repetitive Peak Renerse Voltage	V_{RRM}	Ta=25°C, I_R =0.1mA	10	kV
Average Output Current	I_O	Ta=25°C,Resistive Load	0.6	A peak
Suege Current	I_{FSM}	Ta=25°C,8.3msec, half sine	30	A peak
Junction Temperature	T_j		125	°C
Allowable Operation Case Temperature	Tc		125	°C
Storage Temperature	T_{stg}		-40 to +125	°C

● Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	ESJC60S10	Units
Maximum Forward Voltage Drop	V_F	at 25°C, at: I_F	12	V
Maximum Reverse Current	IR1	at 25°C,V_R =V_{RRM}	5.0	uA
	IR2	at 100°C,V_R =V_{RRM}	50	uA
Maximum Reverse Recovery Time	Trr	at 25°C; I_F =0.5I_R; I_R =I_F(AV); Irr =0.25I_R	--	nS
Junction Capacitance	Cj	at 25°C;V_R=0V,f=1MHz	--	pF